



2811

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PTO/SB/21 (08-00)

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

Application Number	09/535,015
Filing Date	March 24, 2000
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2811
Examiner Name	S. Crane
Attorney Docket Number	0756-2131

ENCLOSURES (check all that apply)

- Fee Transmittal Form
- Fee Attached
- Amendment / Reply
- After Final
- Affidavits/declaration(s)
- Extension of Time Request
- Express Abandonment Request
- Information Disclosure Statement
- Certified Copy of Priority Document(s)
- Response to Missing Parts/ Incomplete Application
- Response to Missing Parts under 37 CFR 1.52 or 1.53

- Assignment Papers (for an Application)
- Drawing(s)
- Declaration and Power of Attorney
- Licensing-related Papers
- Petition
- Petition to Convert to a Provisional Application
- Power of Attorney, Revocation Change of Correspondence Address
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- After Allowance Communication to Group
- Appeal Communication to Board of Appeals and Interferences
- Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)
- Proprietary Information
- Status Letter
- Other Enclosures
 1. Correction to Previously Submitted Information Disclosure with PTO 1449 Form
 - 2.
 - 3.
 - 4.
 - 5.
 - 6.

Remarks

The Commissioner is hereby authorized to charge any additional fees required or credit any overpayments to Deposit Account No. 50-2280 for the above identified docket number.

SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165
Signature	
Date	August 3, 2006

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Attorney Docket No. 0756-2131

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

The Patent Application of:) Group Art Unit: 2811
Shunpei YAMAZAKI et al.) Examiner: S. Crane
Serial No. 09/535,015) CERTIFICATE OF MAILING
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Adel M. Stamer

INFORMATION DISCLOSURE STATEMENT AND CORRECTION OF PREVIOUSLY
SUBMITTED INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

It has come to applicant's attention that several Information Disclosure Statements previously submitted included inadvertent typographical errors or incomplete information.

Specifically, the Information Disclosure Statement filed December 19, 2000 included the following inaccuracies:

1) EP 0 178 447 was incorrectly listed with a publication date of 09/10/1984.

The correct publication date is 04/23/1986; and

2) Several articles did not include an appropriate title, page number, spelling of the author's name, or publication.

The Information Disclosure Statements filed September 5, 2001 and March 17, 2003 included articles which did not include a publication date and page number.

The above inaccuracies are corrected on the 1449 Form attached hereto. The Examiner is requested to initial the attached PTO Form 1449 evidencing consideration of the above references and line through these references on the previously submitted

Information Disclosure Statements to ensure that the correct information is printed correctly on any issued patent.

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
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(571) 434-6789

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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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Substitute for form 1449A/PTO

Complete if Known

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Application Number

09/535,015

Filing Date

March 24, 2000

First Named Inventor

Shunpei YAMAZAKI et al.

Group Art Unit

2811

Examiner Name

Sara W. Crane

Sheet 1 of 2

Attorney Docket Number

0756-2131

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
		EP	0 178 447			04/23/1986		Eng.

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		STOEMENOS et al., <i>Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold</i> , Appl. Phys. Lett., Volume 58, No. 11, March 18, 1991, Pages 1196-1198.	
		KUZNETSOV et al., <i>Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting from Ion Implantation and Annealing</i> , Nuclear Instruments and Methods in Physics Research, 880/881, 1993, Pages 990-993.	
		HATALIS et al., <i>High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films</i> , IEEE Electron Device Letters, Vol. EDL 8, No. 8, August 1987, Pages 361-364.	
		LAU et al., <i>Solid Phase Epitaxy Silicide-Forming Systems</i> , Thin Solid Films, Volume 47, No. 3, 1977, Pages 313-322.	
		KAWAZU et al., <i>Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon</i> , Japanese Journal of Applied Physics, Volume, 29, No. 4, April 1, 1990, Pages 729-738.	
		HEMPEL et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Volume 85, No. 11, 1993, Pages 921-924.	
		KUO, <i>PD Introduced Lateral Crystallization of Amorphous Silicon Thin Films at Low Temperature</i> , Thin Film Transistor Technologies, Volume 94-35, Pages 116-122.	
		WOLF et al., <i>Silicon Processing for the VLSI Era</i> , Volume 1: Process Technology, Lattice Press, 1986, Pages 207-211.	
		DVURECHENSKIY et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol. (a), Volume 95, No. 635, 1986, Pages 635-640.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Group Art Unit	2811
Examiner Name	Sara W. Crane
Attorney Docket Number	0756-2131

O I P E
AUG. 07 2006
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S E R V I C E C O M M I S S I O N

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet 2 of 2

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²
		Office ³	Number ⁴ (if known)				

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		HAYZELDEN et al., <i>Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films</i> , J. Appl. Phys., Volume 73, No. 12, June 15, 1993, Pages 8279-8289.	
		KUZNETSOV et al., <i>Silicide Precipitate Formation and Solid Phase Re-Growth of Ni⁺-Implanted Amorphous Silicon</i> , Inst. Phys. Conf. Ser. No. 134.4: Proceedings of the Royal Microscopical Society Conf., April 5-8, 1993, Pages 191-194.	
		BAKER, JR. et al., <i>Field Effect Transistor</i> , IBM Technical Disclosure Bulletin, Volume 11, No. 7, December 1968, Page 849.	
		WOLF, <i>Silicon Processing for the VLSI Era</i> , Volume 2: Process Integration, 1990, Pages 273-274.	
		CAUNE et al., <i>Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals</i> , Applied Surface Science, Volume 36, January 1, 1989, Pages 597-604.	

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